

SOT223 PNP SILICON PLANAR HIGH CURRENT (HIGH PERFORMANCE) TRANSISTORS

FZT957
FZT958

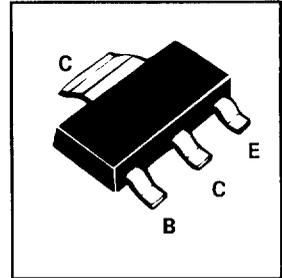
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FEATURES

- * 1 Amp continuous current
- * Up to 2 Amps peak current
- * Very low saturation voltage
- * Excellent gain characteristics specified up to 1 Amp

COMPLEMENTARY TYPES - FZT957 FZT857
FZT958 N/A

PARTMARKING DETAILS - DEVICE TYPE IN FULL



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	FZT957	FZT958	UNIT
Collector-Base Voltage	V_{CBO}	-300	-400	V
Collector-Emitter Voltage	V_{CEO}	-300	-400	V
Emitter-Base Voltage	V_{EBO}	-6		V
Peak Pulse Current	I_{CM}	-2	-1.5	A
Continuous Collector Current	I_C	-1	-0.5	A
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	3		W
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150		$^{\circ}C$

*The power which can be dissipated assuming the device is mounted in a typical manner on a P.C.B. with copper equal to 4 square inch minimum

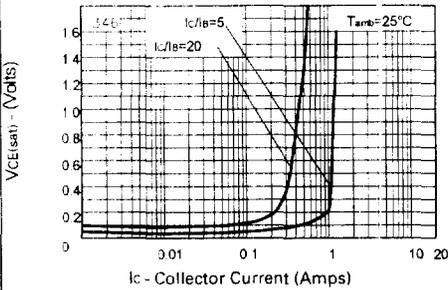
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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

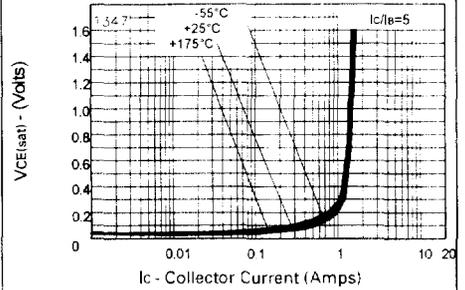
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-330	-440		V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CER}$	-330	-440		V	$I_C = -1\mu\text{A}$, $R_B \leq 1\text{k}\Omega$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-300	-400		V	$I_C = -10\text{mA}^*$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-6	-8		V	$I_E = -100\mu\text{A}$
Collector Cut-Off Current	I_{CBO}			-50 -1	nA μA	$V_{CB} = -300\text{V}$ $V_{CB} = -300\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Collector Cut-Off Current	I_{CER} $R \leq 1\text{k}\Omega$			-50 -1	nA μA	$V_{CB} = -300\text{V}$ $V_{CB} = -300\text{V}$, $T_{amb} = 100^{\circ}\text{C}$
Emitter Cut-Off Current	I_{EBO}			-10	nA	$V_{EB} = -6\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-60 -110 -170	-100 -165 -240	mV mV mV	$I_C = -100\text{mA}$, $I_B = -10\text{mA}^*$ $I_C = -500\text{mA}$, $I_B = -100\text{mA}^*$ $I_C = -1\text{A}$, $I_B = -300\text{mA}^*$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-910	-1150	mV	$I_C = -1\text{A}$, $I_B = -300\text{mA}^*$
Base-Emitter Turn-On Voltage	$V_{BE(on)}$		-750	-1020	mV	$I_C = -1\text{A}$, $V_{CE} = -10\text{V}^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 90	200 200 170 10	300		$I_C = -10\text{mA}$, $V_{CE} = -10\text{V}^*$ $I_C = -0.5\text{A}$, $V_{CE} = -10\text{V}^*$ $I_C = -1\text{A}$, $V_{CE} = -10\text{V}^*$ $I_C = -2\text{A}$, $V_{CE} = -10\text{V}^*$
Transition Frequency	f_T		85		MHz	$I_C = -100\text{mA}$, $V_{CE} = -10\text{V}$ $f = 50\text{MHz}$
Output Capacitance	C_{obo}		23		pF	$V_{CB} = -20\text{V}$, $f = 1\text{MHz}$
Switching Times	t_{on} t_{off}		108 2500		ns ns	$I_C = -500\text{mA}$, $I_{B1} = -50\text{mA}$ $I_{B2} = 50\text{mA}$, $V_{CC} = -100\text{V}$

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device

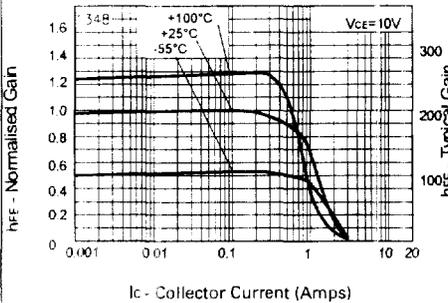
TYPICAL CHARACTERISTICS



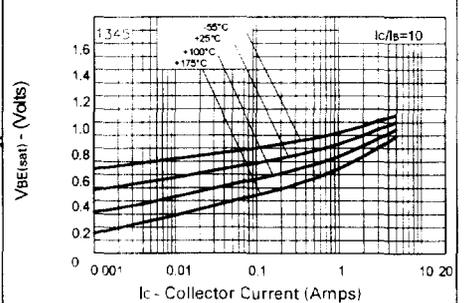
$V_{CE(sat)}$ v I_C



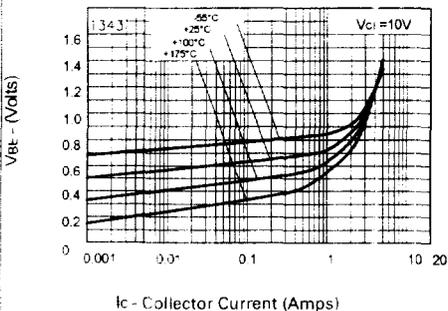
$V_{CE(sat)}$ v I_C



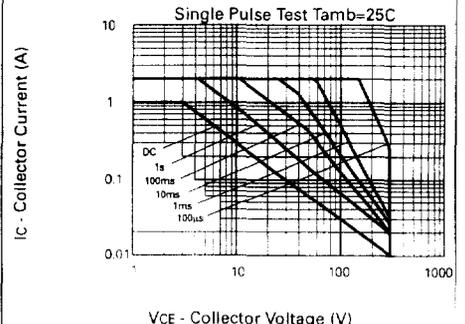
h_{FE} v I_C



$V_{BE(sat)}$ v I_C



$V_{BE(on)}$ v I_C



Safe Operating Area